

**IN THE CLAIMS:**

Please cancel claims 15-16, 19-20, and 24-28, and amend the claims as follows:

1-13 (Cancelled)

14. (Currently Amended) A method of forming a contact ring, comprising:

providing ~~[[a]]~~ an annular substrate;

depositing at least ~~a first one~~ one conductive layer on the annular substrate, wherein said ~~first~~ conductive layer coats ~~a all~~ support surface~~[[s]]~~ of the annular substrate; ~~[[and]]~~

depositing at least ~~a first one~~ one insulative layer adjacent to the ~~at least a first~~ conductive layer, on the annular substrate, wherein said ~~first~~ insulative layer coats all surfaces of the substrate conductive layer; and

electrically connecting a contact to the conductive layer through said insulative layer on the annular substrate.

15-16. (Cancelled)

17. (Currently Amended) The method of claim 14 ~~[[16]]~~, further comprising ~~electrically connecting a contact to at least one of the conductive layers, wherein the~~ depositing a compliant ridge extends around the periphery of that surrounds the contact.

18. (Currently Amended) A contact ring for providing electrical contact between a wafer and a power supply, comprising:

a conductive layer positioned on at least one support surface of an annular substrate;

an insulative layer deposited above the conductive layer;

a contact in electrical contact with the conductive layer and extending through the insulative layer above the conductive layer to an external surface; and

a compliant ridge formed on the external surface, and extending about the periphery of the contact.

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19-28. (Cancelled)

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